

# 2SC1317, 2SC1318

## Silicon NPN epitaxial planer type

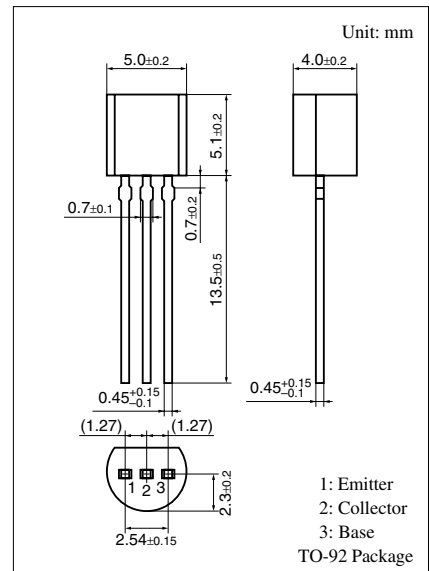
For low-frequency power amplification and driver amplification  
Complementary to 2SA719 and 2SA720

### ■ Features

- Low collector to emitter saturation voltage  $V_{CE(sat)}$
- Complementary pair with 2SA719 and 2SA720

### ■ Absolute Maximum Ratings $T_a = 25^\circ\text{C}$

Parameter	Symbol	Rating	Unit
Collector to base voltage	2SC1317	30	V
	2SC1318	60	
Collector to emitter voltage	2SC1317	25	V
	2SC1318	50	
Emitter to base voltage	$V_{EBO}$	7	V
Peak collector current	$I_{CP}$	1	A
Collector current	$I_C$	500	mA
Collector power dissipation	$P_C$	625	mW
Junction temperature	$T_j$	150	$^\circ\text{C}$
Storage temperature	$T_{stg}$	-55 to +150	$^\circ\text{C}$



### ■ Electrical Characteristics $T_a = 25^\circ\text{C} \pm 3^\circ\text{C}$

Parameter	Symbol	Conditions	Min	Typ	Max	Unit
Collector cutoff current	$I_{CBO}$	$V_{CB} = 20\text{ V}, I_E = 0$			0.1	$\mu\text{A}$
Collector to base voltage	$V_{CBO}$	$I_C = 10\ \mu\text{A}, I_E = 0$	30			V
			60			
Collector to emitter voltage	$V_{CEO}$	$I_C = 10\ \text{mA}, I_B = 0$	25			V
			50			
Emitter to base voltage	$V_{EBO}$	$I_E = 10\ \mu\text{A}, I_C = 0$	7			V
Forward current transfer ratio *1	$h_{FE1}$ *2	$V_{CE} = 10\ \text{V}, I_C = 150\ \text{mA}$	85		340	
	$h_{FE2}$	$V_{CE} = 10\ \text{V}, I_C = 500\ \text{mA}$	40			
Collector to emitter saturation voltage *1	$V_{CE(sat)}$	$I_C = 300\ \text{mA}, I_B = 30\ \text{mA}$		0.35	0.6	V
Base to emitter saturation voltage *1	$V_{BE(sat)}$	$I_C = 300\ \text{mA}, I_B = 30\ \text{mA}$		1.1	1.5	V
Transition frequency	$f_T$	$V_{CB} = 10\ \text{V}, I_E = -50\ \text{mA}, f = 200\ \text{MHz}$		200		MHz
Collector output capacitance	$C_{ob}$	$V_{CB} = 10\ \text{V}, I_E = 0, f = 1\ \text{MHz}$		6	15	pF

Note) \*1: Pulse measurement

\*2: Rank classification

Rank	Q	R	S
$h_{FE1}$	85 to 170	120 to 240	170 to 340

